Last updated 3/8/23

• Real diode behavior



Real diode behavior



 $V_D > V_Z$ $I_D = I_S \left(e^{\frac{V_D}{nV_T}} - 1 \right)$

- Ideal diode models
 - Switch model

	Forward Bias
Rever <mark>se</mark> Bias	Threshold voltage = 0V

L Ideal $\mathbf{\nabla}$

- Ideal diode models
 - Switch model with Turn-on voltage



- Ideal diode models
 - Piecewise Linear model



- Small Signal Model
 - Consider the I-V characteristics constant



Small Signal Model

small $\Delta v \rightarrow$ large Δi $I_D - DC$ current $V_D - DC$ voltage $i_d - small signal current$ $v_d - small signal voltage$ $\frac{1}{1} \quad \stackrel{}{\longleftrightarrow} \quad \stackrel{}{\underset{d}{\longrightarrow}} \quad$

large $\Delta v \rightarrow$ small Δi

$$i_{d} = \left(\frac{I_{D}}{V_{T}}\right)v_{d} = \left(\frac{1}{r_{d}}\right)$$
$$r_{d} = \left(\frac{V_{T}}{I_{D}}\right)$$

 C_j – Junction Capacitance C_d – Diffusion Capacitance

 C_j – dominant in reverse bias C_d – dominant in forward bias

 v_d